

N-channel TrenchMOS standard level FET

Rev. 02 — 18 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

	duler reference du					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	41	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	149	W
Static char	racteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 175 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$	-	-	88	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \text{ see } \overline{Figure \ 12}; \\ \text{see } \overline{Figure \ 13} \end{array}$	-	21	35	mΩ
Avalanche	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 25 \text{ A}; \text{V}_{sup} \leq 100 \text{ V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	110	mJ

Suitable for standard level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
BUK7635-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1;</u> see <u>Figure 3</u>	-	41	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	29	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	165	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	149	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	41	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	165	А
Avalanche	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 25 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	110	mJ

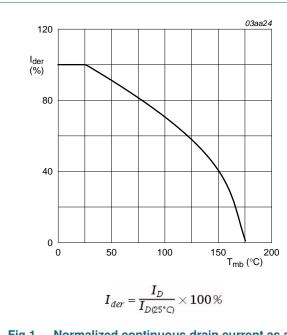


Fig 1. Normalized continuous drain current as a function of mounting base temperature

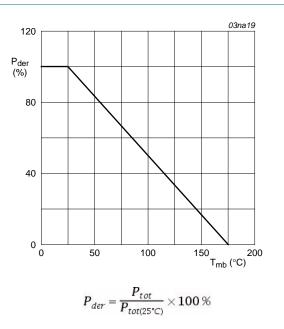
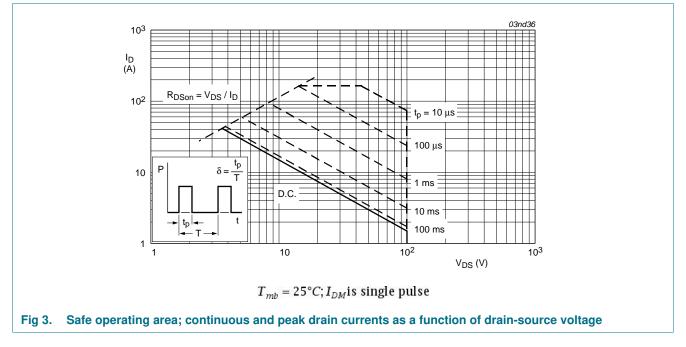


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK7635-100A

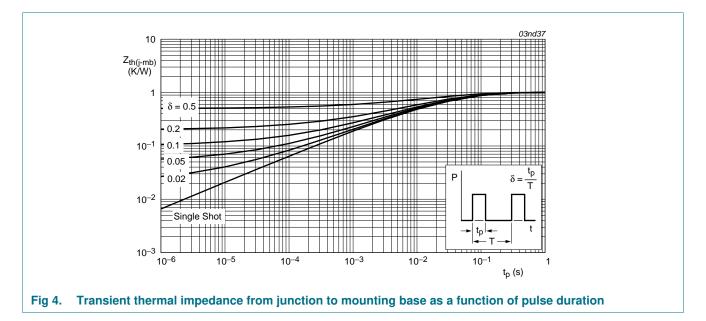
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



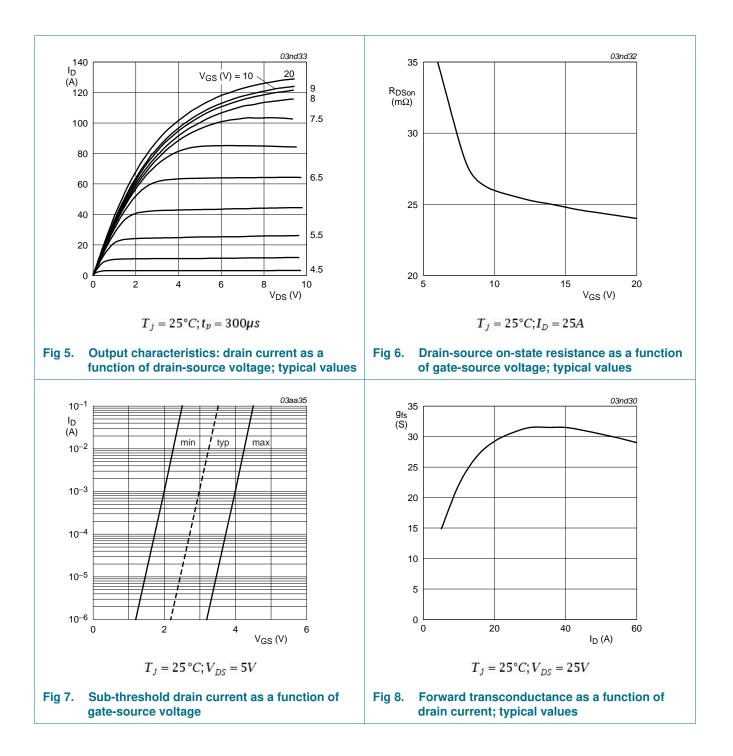
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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS} drain-source		I _D = 0.25 A; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 0.25 A; V _{GS} = 0 V; T _j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
Boon	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	88	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	21	35	mΩ
Dynamic ch	aracteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1900	2535	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	250	301	pF
C _{rss}	reverse transfer capacitance		-	150	205	pF
t _{d(on)}	turn-on delay time		-	15	-	ns
t _r	rise time		-	67	-	ns
t _{d(off)}	turn-off delay time	V_{DS} = 30 V; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω	-	56	-	ns
t _f	fall time		-	35	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-drai	n diode					
V _{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	67	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	220	-	nC

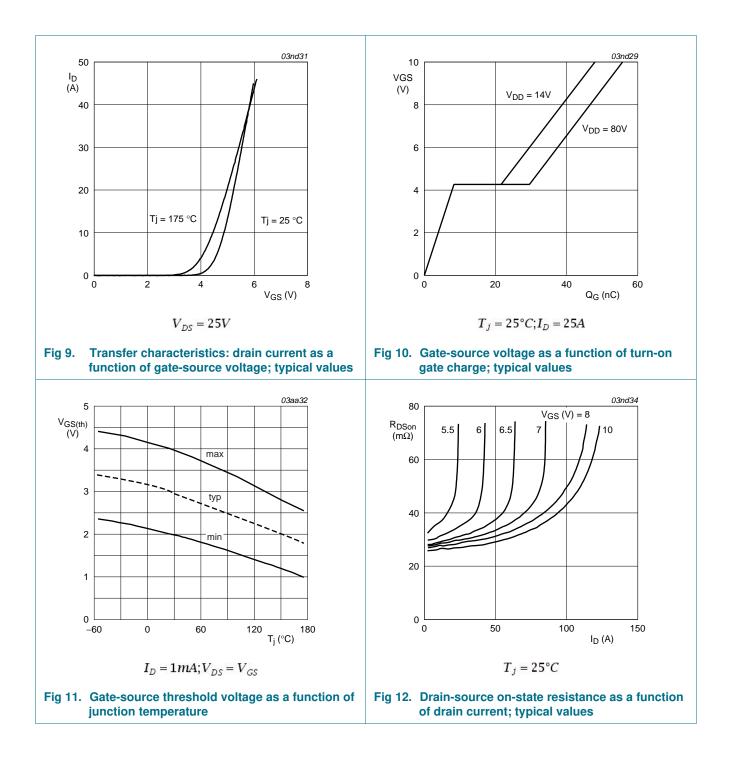
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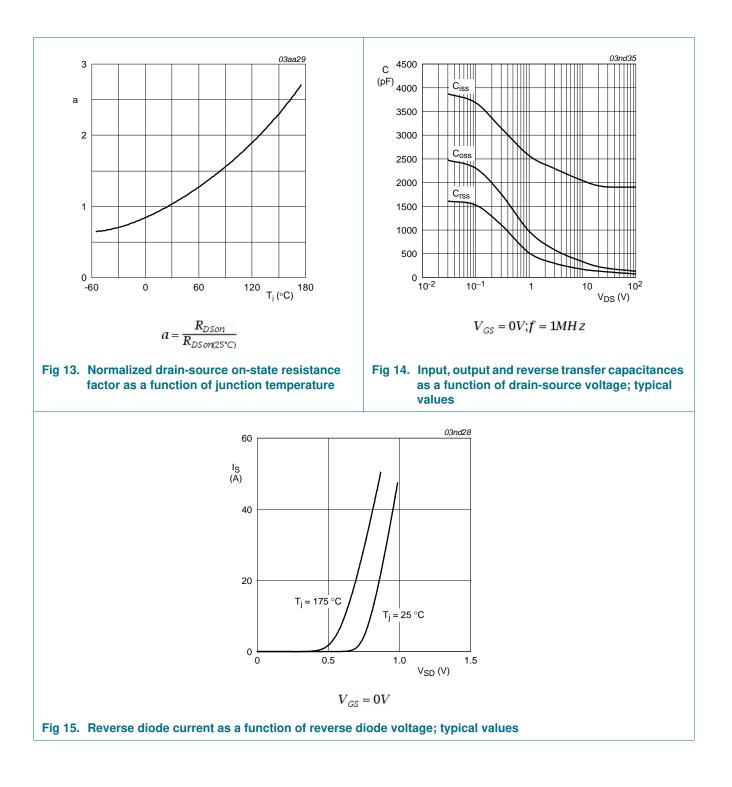
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7. Package outline

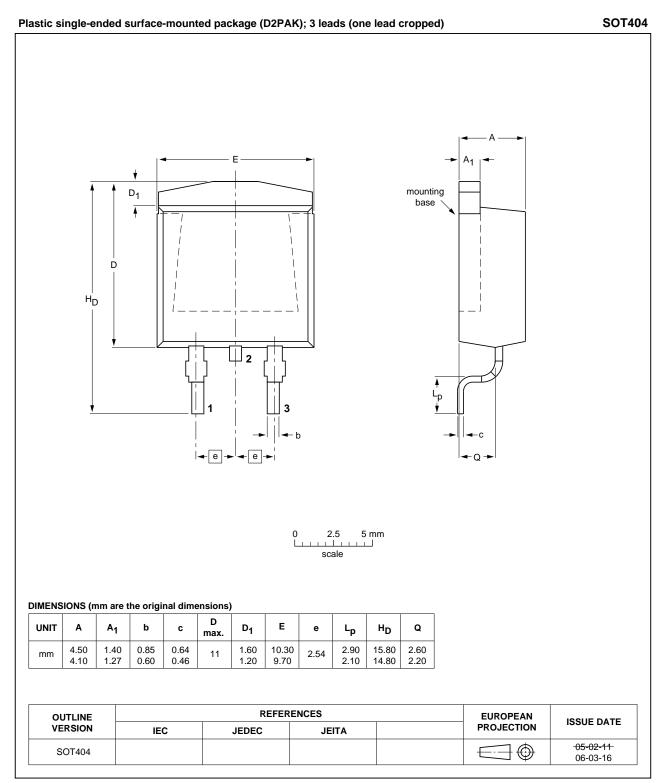


Fig 16. Package outline SOT404 (D2PAK)

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Product data sheet

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8. Revision history

Table 7. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7635-100A v.2	20110218	Product data sheet	-	BUK7535_7635_100A v.1
Modifications:	guidelines of NX • Legal texts have	nis data sheet has been re XP Semiconductors. e been adapted to the ne	w company name wh	ere appropriate.
	 Type number B 	UK7635-100A separated	from data sheet BUK	(7535_7635_100A v.1.
BUK7535_7635_100A v.1	20010202	Product specification	-	-

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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